Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	(low near dose near nitrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:28
L2	5	(low near dose near nitrogen) near25 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:32
L3	34765	(nitrogen) near25 (substrate or wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:33
L4	1882	3 and (low near3 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:33
L5	141	3 and (low near3 voltage near3 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:46
L6	0	3 and ((low near3 voltage near3 region)) near25 (dielectri or inulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:34
L7	10	3 and ((low near3 voltage near3 region)) near25 (dielectric or inulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:34
L8	843	3 and (voltage near3 region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:46
L9	0	3 and ((voltage near3 region) near5 (intermediate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:47

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L10	4	3 and ((voltage near3 region) near15 (intermediate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:48
L11	605	(low near voltage) near15 (high near voltage) near15 (intermediate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 18:05
L12	19	11 and (gate near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 17:49
L13	1022	(low near voltage) near15 (high near voltage) near15 (core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:26
L14	26	13 and (gate near3 dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 18:05
L15	14	14 and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 18:05
L16	369	13 and (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:24
L17	0	16 and (tri-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:21
L18	. 0	13 and (tri-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:21
L19	0	13 and (tri near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:21

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L20	0	16 and (tri near gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:21
L21	3	13 and ((source or drain) near25 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:27
L22	42324	(low near voltage) near15 (high near voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:31
L23	405	22 and ((source or drain) near25 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:27
L24	379	22 and ((source or drain) near15 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:31
L25	0	24 and (tri-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:27
L26	46	24 and (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:32
L27	76007	(low near3 voltage) near15 (high near3 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:31
L28	722	27 and ((source or drain) near15 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:31
L29	114	28 and (gate near dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:38

L30	77	(tri-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:40
L31	65	30 and (sour or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:38
L32	2	30 and ((sour or drain) near15 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:39
L33	0	30 and ((sour or drain) near15 (inter-connect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:39
L34	0	((tri-gate) near15 (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:40
L35	28	((tri-gate) and (interconnect\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/14 19:40